

SIPMOS® Power-Transistor

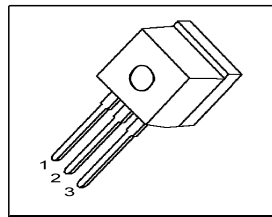
Feature

- N-Channel
- Enhancement mode
- Logic Level
- 175°C operating temperature
- Avalanche rated
- dv/dt rated

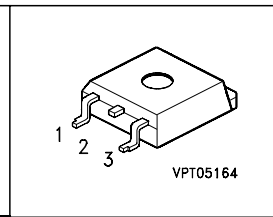
Product Summary

V_{DS}	100	V
$R_{DS(on)}$	26	mΩ
I_D	47	A

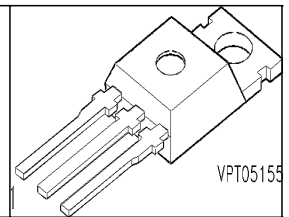
P-TO262-3-1



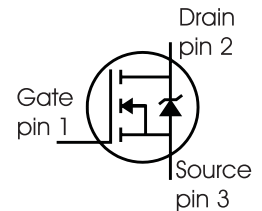
P-TO263-3-2



P-TO220-3-1



Type	Package	Ordering Code	Marking
IPP47N10SL-26	PG-TO220-3-1	SP0002-25707	N10L26
IPB47N10SL-26	PG-TO263-3-2	SP0002-25701	N10L26
IPI47N10SL-26	PG-TO262-3-1	SP0002-25704	N10L26



Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D	47	A
$T_C=25\text{ °C}$		47	
$T_C=100\text{ °C}$		33	
Pulsed drain current	$I_D \text{ puls}$	188	
$T_C=25\text{ °C}$			
Avalanche energy, single pulse	E_{AS}	400	mJ
$I_D=47\text{ A}$, $V_{DD}=25\text{ V}$, $R_{GS}=25\text{ Ω}$			
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	17.5	
Reverse diode dv/dt	dv/dt	6	kV/μs
$I_S=47\text{ A}$, $V_{DS}=0\text{ V}$, $di/dt=200\text{ A/μs}$			
Gate source voltage	V_{GS}	±20	V
Power dissipation	P_{tot}	175	W
$T_C=25\text{ °C}$			
Operating and storage temperature	T_j, T_{stg}	-55... +175	°C
IEC climatic category; DIN IEC 68-1		55/175/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	0.85	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	62	
@ 6 cm ² cooling area ¹⁾		-	-	40	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0V, I_D=2mA$	$V_{(BR)DSS}$	100	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 2 mA$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS}=100V, V_{GS}=0V, T_j=25^\circ\text{C}$ $V_{DS}=100V, V_{GS}=0V, T_j=150^\circ\text{C}$	I_{DSS}	-	0.1	1	μA
		-	-	100	
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	10	100	nA
Drain-source on-state resistance $V_{GS}=4.5V, I_D=33A$	$R_{DS(on)}$	-	25	40	m Ω
Drain-source on-state resistance $V_{GS}=10V, I_D=33A$	$R_{DS(on)}$	-	18	26	

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 33\text{A}$	18	36	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	2000	2500	pF
Output capacitance	C_{oss}		-	375	470	
Reverse transfer capacitance	C_{rss}		-	210	265	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{V}$, $V_{GS} = 4.5\text{V}$, $I_D = 47\text{A}$, $R_G = 2\Omega$	-	50	75	ns
Rise time	t_r		-	100	150	
Turn-off delay time	$t_{d(off)}$		-	50	75	
Fall time	t_f		-	70	105	

Gate Charge Characteristics

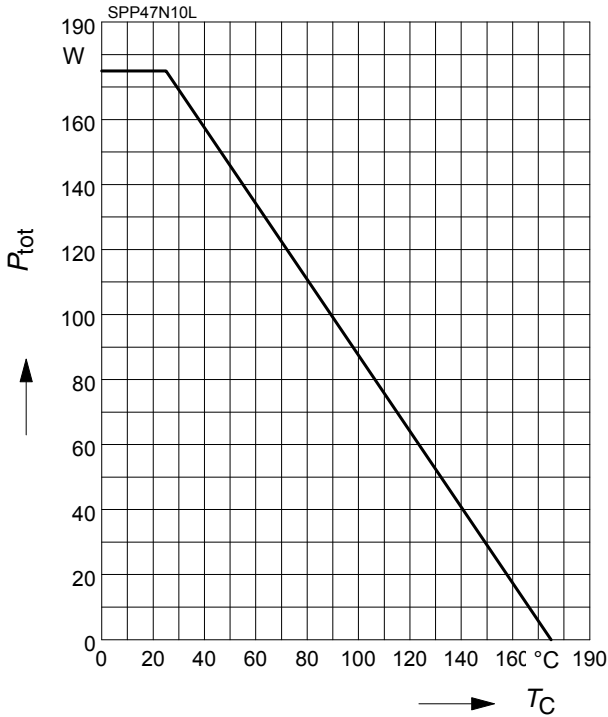
Gate to source charge	Q_{gs}	$V_{DD} = 80\text{V}$, $I_D = 47\text{A}$	-	8	12	nC
Gate to drain charge	Q_{gd}		-	16	24	
Gate charge total	Q_g	$V_{DD} = 80\text{V}$, $I_D = 47\text{A}$, $V_{GS} = 0$ to 10V	-	90	135	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 80\text{V}$, $I_D = 47\text{A}$	-	3.38	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_C = 25^\circ\text{C}$	-	-	47	A
Inverse diode direct current, pulsed	I_{SM}		-	-	188	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}$, $I_F = 94\text{A}$	-	1.1	1.5	V
Reverse recovery time	t_{rr}	$V_R = 50\text{V}$, $f = 5$, $di_F/dt = 100\text{A}/\mu\text{s}$	-	80	120	ns
Reverse recovery charge	Q_{rr}		-	340	510	nC

1 Power dissipation

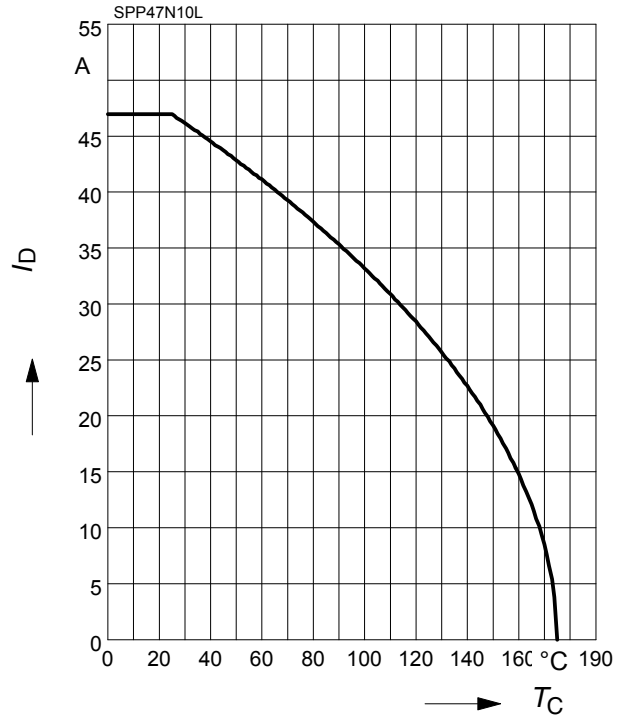
$$P_{tot} = f(T_C)$$



2 Drain current

$$I_D = f(T_C)$$

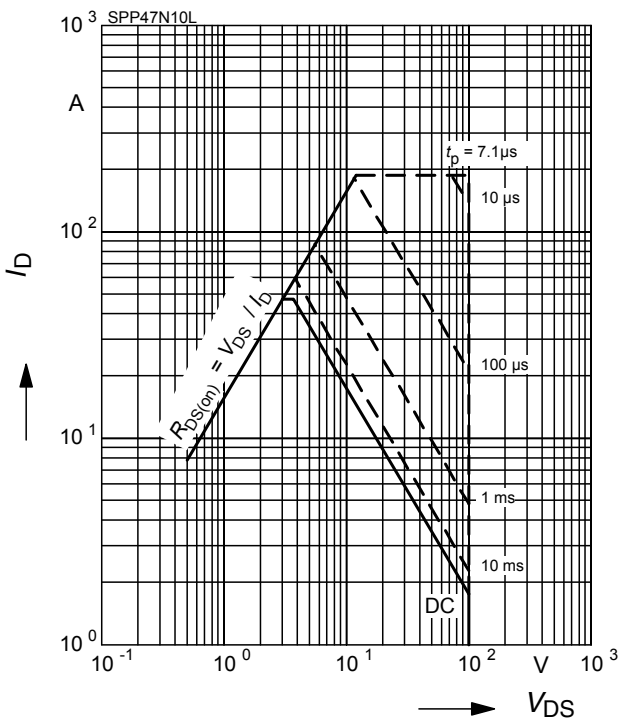
parameter: $V_{GS} \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

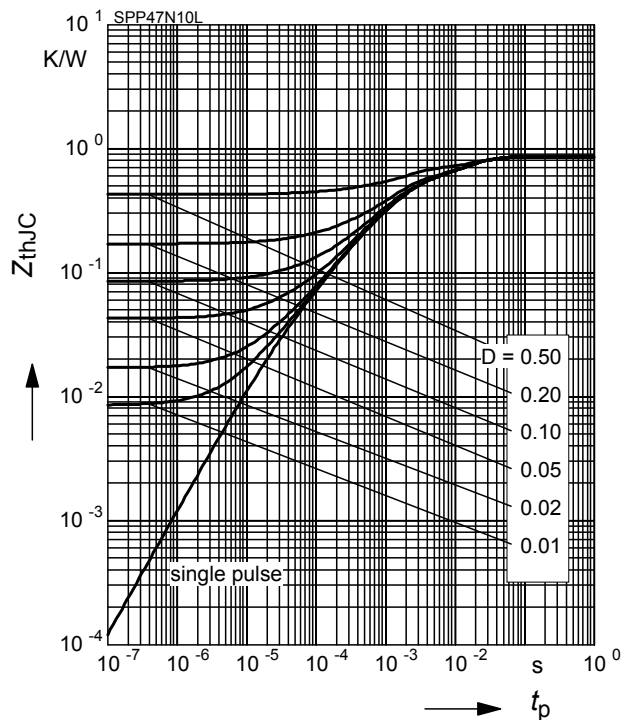
parameter: $D = 0, T_C = 25 \text{ °C}$



4 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

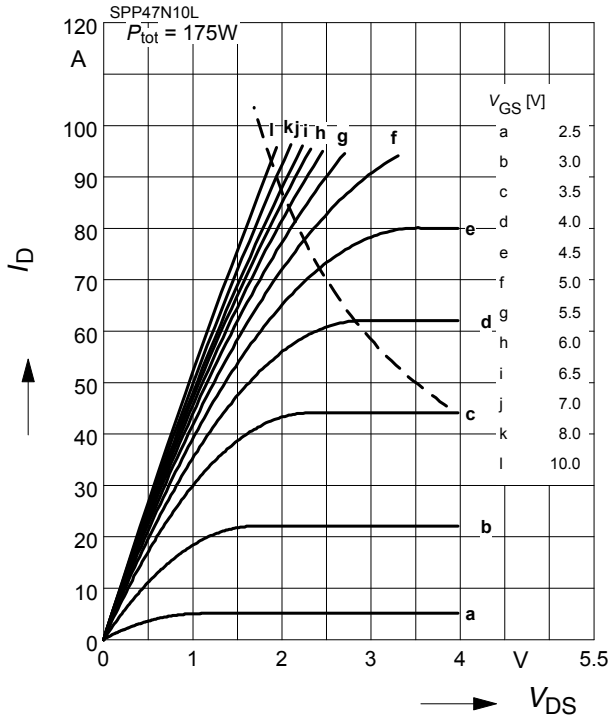
parameter: $D = t_p/T$



5 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

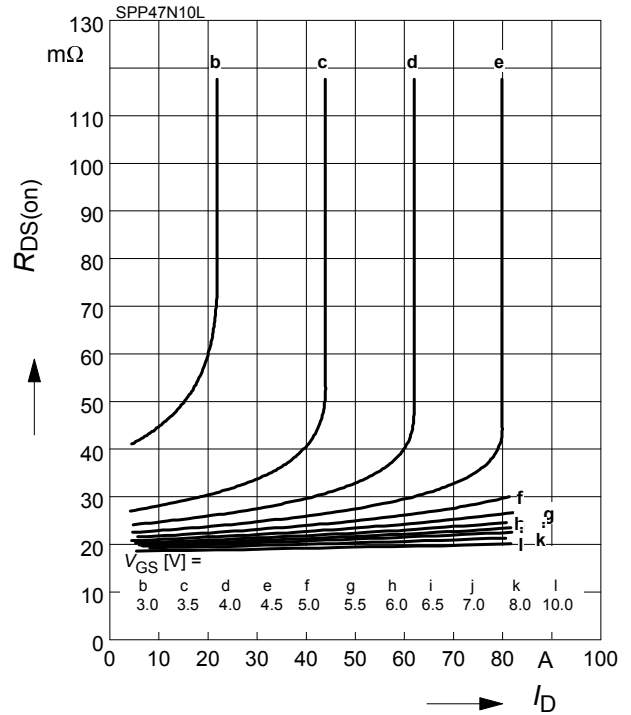
parameter: $t_p = 80 \mu\text{s}$



6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

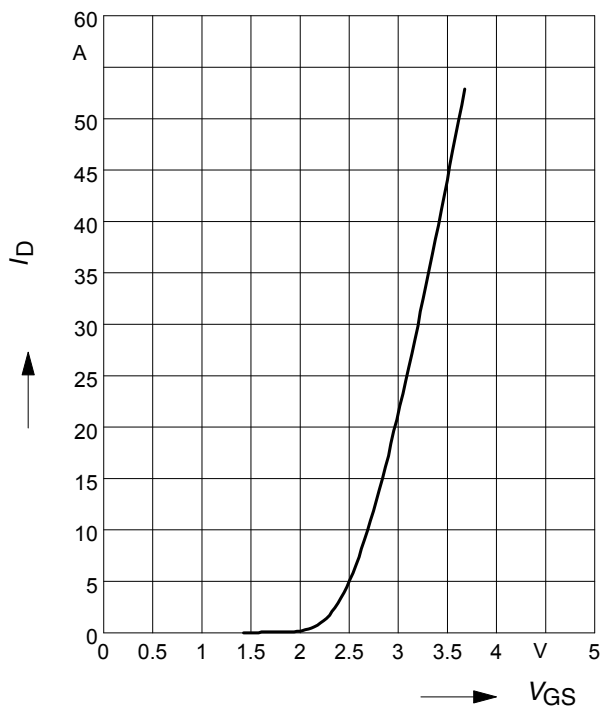
parameter: V_{GS}



7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

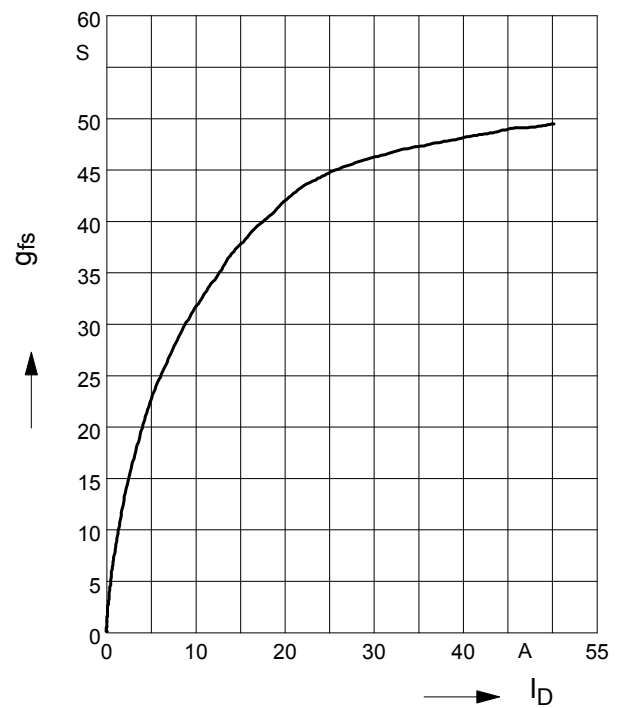
parameter: $t_p = 80 \mu\text{s}$



8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$

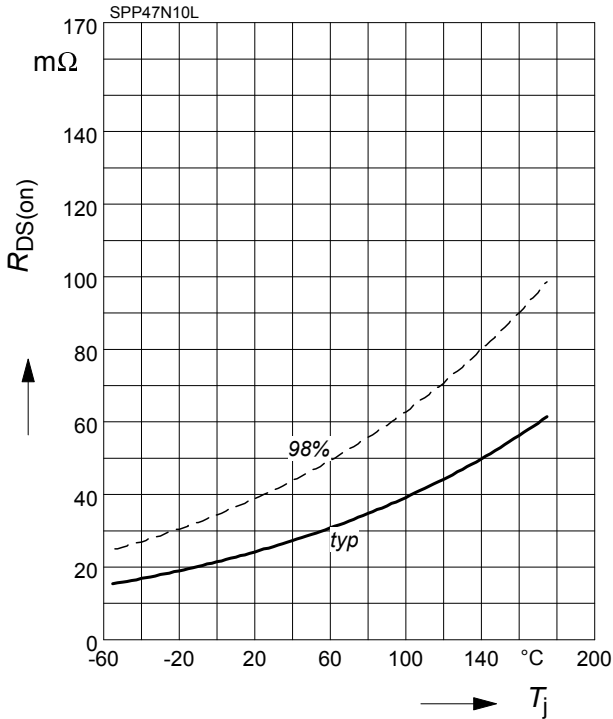
parameter: g_{fs}



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

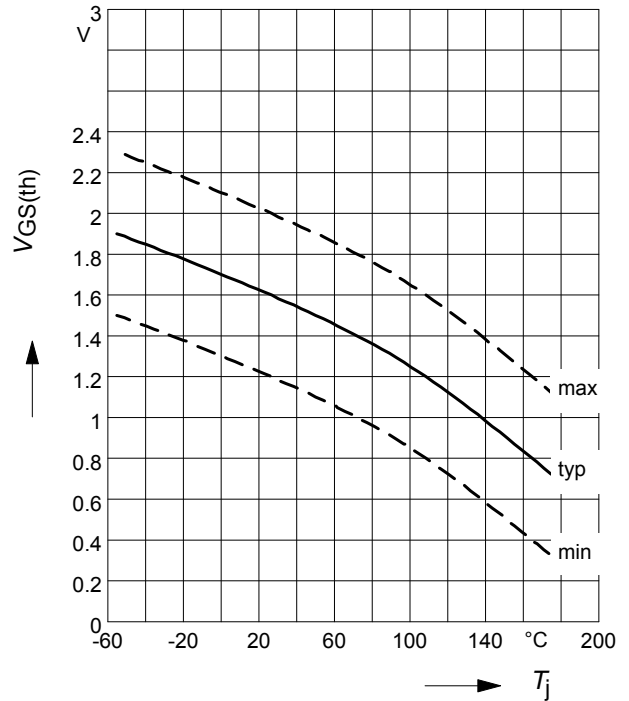
parameter: $I_D = 33\text{ A}$, $V_{GS} = 4.5\text{ V}$



10 Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

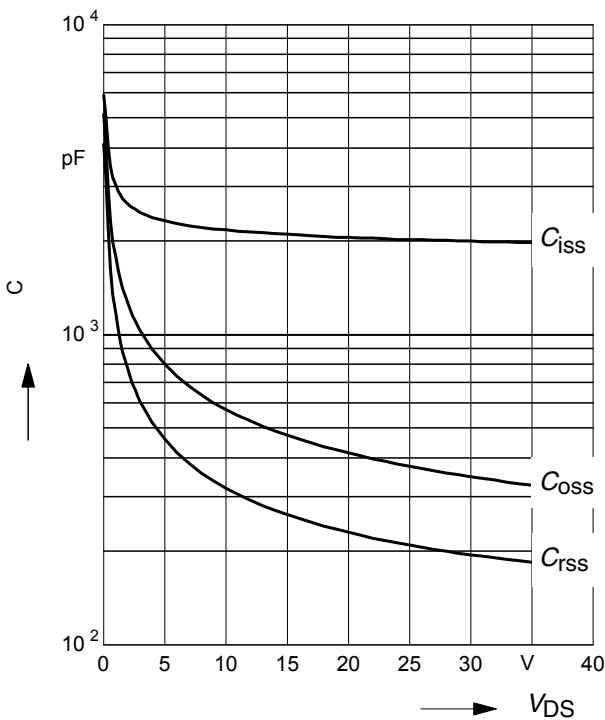
parameter: $V_{GS} = V_{DS}$, $I_D = 2\text{ mA}$



11 Typ. capacitances

$$C = f(V_{DS})$$

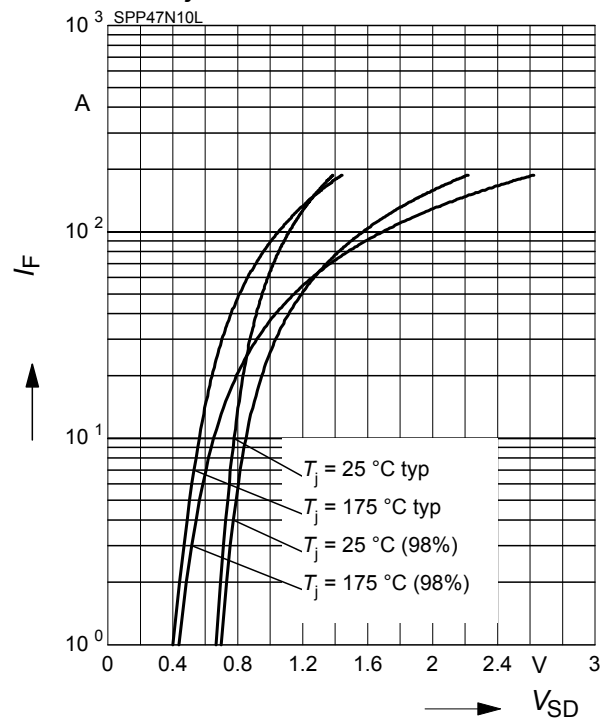
parameter: $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

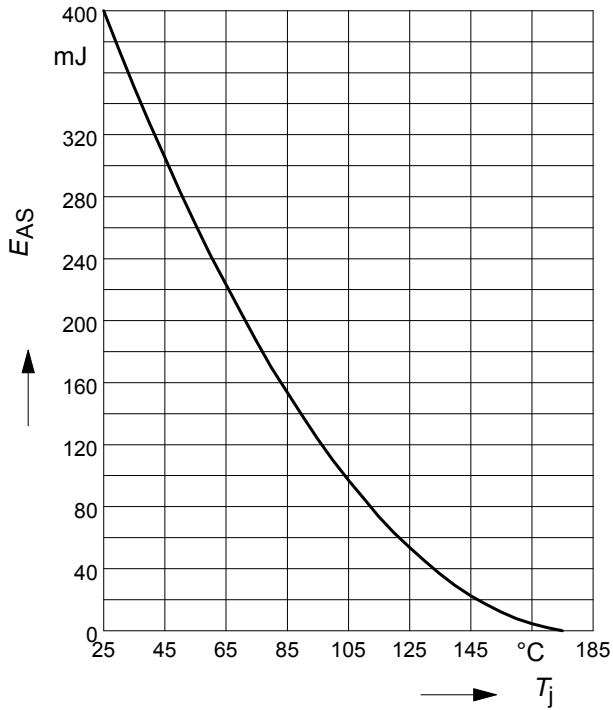
parameter: T_j , $t_p = 80\text{ }\mu\text{s}$



13 Typ. avalanche energy

$$E_{AS} = f(T_j)$$

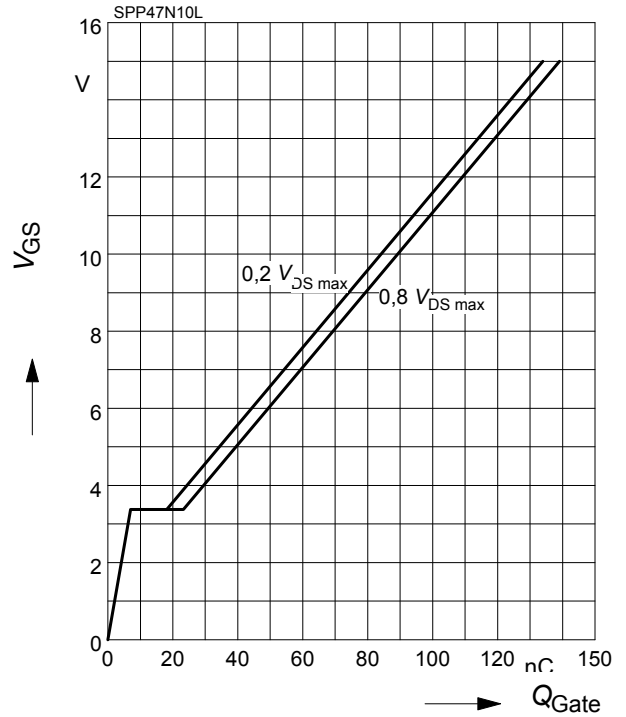
par.: $I_D = 47\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\ \Omega$



14 Typ. gate charge

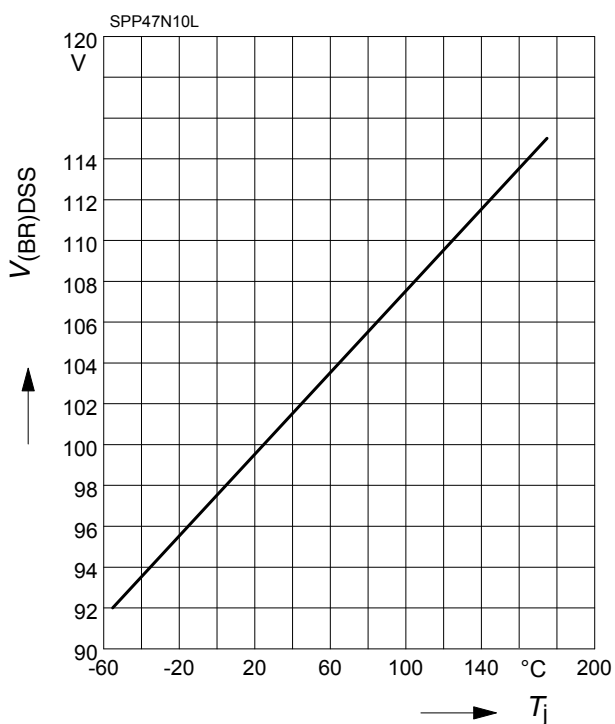
$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = 47\text{ A}$ pulsed



15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$



Published by
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Bereichs Kommunikation
St.-Martin-Strasse 53,
D-81541 München
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